



ZXMS6004FFQ

60V N-CHANNEL SELF PROTECTED ENHANCEMENT MODE IntelliFET MOSFET

Product Summary

- Continuous Drain Source Voltage: 60V
- On-State Resistance: 500mΩ
- Nominal Load Current (VIN = 5V): 1.3A
- Clamping Energy: 90mJ

Description

The ZXMS6004FFQ is a self-protected low side IntelliFET[™] MOSFET with logic level input. It integrates overtemperature, overcurrent, overvoltage (active clamp) and ESD protected logic level functionality. The ZXMS6004FFQ is ideal as a general purpose switch driven from 3.3V or 5V microcontrollers in harsh environments where standard MOSFETs are not rugged enough.

Applications

- Especially Suited for Loads with a High In-Rush Current such as Lamps and Motors
- All Types of Resistive, Inductive and Capacitive Loads in Switching Applications
- µC Compatible Power Switch for 12V and 24V DC Applications
- Automotive Rated
- Replaces Electromechanical Relays and Discrete Circuits
- Linear Mode Capability the current-limiting protection circuitry is designed to de-activate at low V_{DS} to minimize on state power dissipation. The maximum DC operating current is therefore determined by the thermal capability of the package/board combination, rather than by the protection circuitry. This does not compromise the product's ability to self-protect at low V_{DS}.

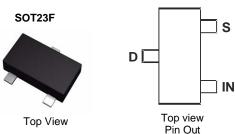
Features and Benefits

- Compact High Power Dissipation Package
- Low Input Current
- Logic Level Input (3.3V and 5V)
- Short Circuit Protection with Auto Restart
- Over Voltage Protection (Active Clamp)
- Thermal Shutdown with Auto Restart
- Overcurrent Protection
- Input Protection (ESD)
- High Continuous Current Rating
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The ZXMS6004FFQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: SOT23F
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish @3
- Weight: 0.012 grams (Approximate)



Ordering Information (Note 4)

Notes:

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXMS6004FFQTA	1K6	7	12	3,000
ZXMS6004FFQ-7	1K6	7	8	3,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

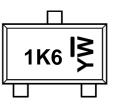
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

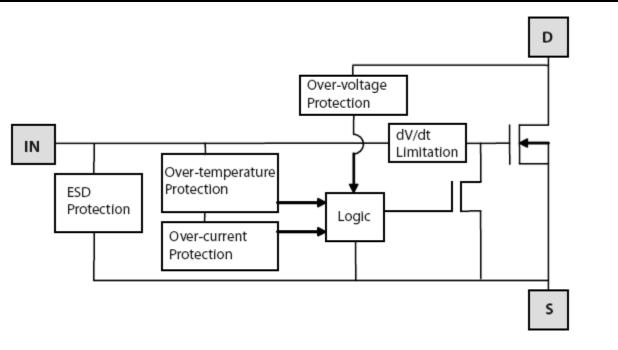


Marking Information



 $\begin{array}{l} 1 \text{K6} = \text{Product Type Marking Code} \\ \text{Y or } \overline{\text{Y}:} \quad \text{Year: 0 to 9} \\ \text{W or } \overline{\text{W}:} \quad \text{Week: A to } \text{Z}: 1 \text{ to 26} \\ \text{a to } \text{z}: 27 \text{ to 52} \\ \text{z: Represents 52 \& 53 Week} \end{array}$

Functional Block Diagram





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Continuous Drain-Source Voltage	VDS	60	V	
Drain-Source Voltage for Short Circuit Protection	V _{DS(SC)}	36	V	
Continuous Input Voltage	VIN	-0.5 +6	V	
Continuous Input Current @-0.2V $\leq V_{IN} \leq 6V$		No Limit	mA	
Continuous Input Current @VIN < -0.2V or VIN > 6V	lin	I _{IN} ≤2	IIIA	
Pulsed Drain Current @VIN = 3.3V	Ідм	2	А	
Pulsed Drain Current @VIN = 5V	Ідм	2.5	А	
Continuous Source Current (Body Diode)	Is	1	А	
Pulsed Source Current (Body Diode)	I _{SM}	5	A	
Unclamped Single Pulse Inductive Energy,	F	90	ml	
$T_J = +25^{\circ}C, I_D = 0.5A, V_{DD} = 24V$	Eas	90	mJ	
Electrostatic Discharge (Human Body Model)	V _{ESD}	4,000	V	
Charged Device Model	Vcdm	1,000	V	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation $@T_A = +25^{\circ}C$ (Note 5) Linear Derating Factor	PD	0.83 6.66	W mW/°C
Power Dissipation @T _A = +25°C (Note 6) Linear Derating Factor	PD	1.5 12.0	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	150	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	Reja	83	°C/W
Thermal Resistance, Junction to Case (Note 7)	Rejc	44	°C/W
Operating Temperature Range	TJ	-40 to +150	٥°C
Storage Temperature Range	Tstg	-55 to +150	٥°C

Recommended Operating Conditions

The ZXMS6004FFQ is optimized for use with μ C operating from 3.3V and 5V supplies.

Characteristic	Symbol	Min	Max	Unit
Input Voltage Range	Vin	0	5.5	V
Ambient Temperature Range	TA	-40	+125	°C
High Level Input Voltage for MOSFET to be On	VIH	3	5.5	V
Low Level Input Voltage for MOSFET to be Off	VIL	0	0.7	V
Peripheral Supply Voltage (Voltage to Which Load is Referred)	VP	0	36	V

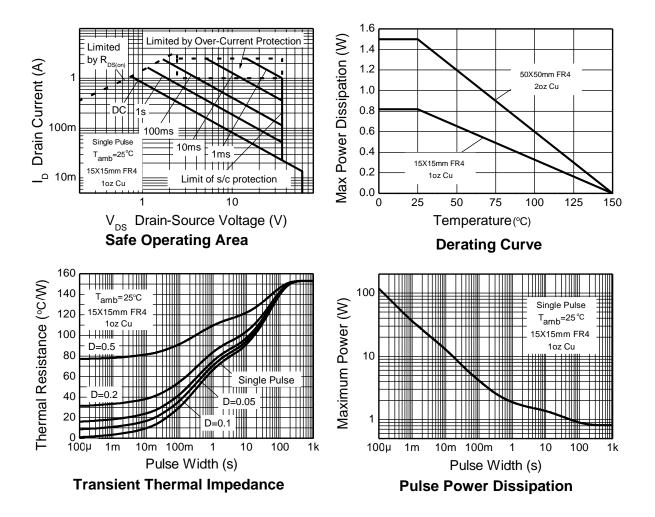
Notes:

For a device surface mounted on 15mm x 15mm single sided, 1oz weight copper on 1.6mm FR4 board, in still air conditions.
 For a device surface mounted on 50mm x 50mm single sided, 2oz weight copper on 1.6mm FR4 board, in still air conditions.

7. Thermal resistance from junction and the mounting surfaces of the drain pins.



Typical Thermal Characteristics



Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Static Characteristics	Cymbol	WITT	Typ	Max	Onit	Test condition
Drain-Source Clamp Voltage	VDS(AZ)	60	65	70	V	$I_{\rm D} = 10 {\rm mA}$
	IDSS -	_	—	500	nA	$V_{DS} = 12V, V_{IN} = 0V$
Off-State Drain Current		_	—	1	μA	$V_{DS} = 36V, V_{IN} = 0V$
Input Threshold Voltage	VIN(TH)	0.7	1	1.5	V	V _{DS} = V _{GS} , I _D = 1mA
Innut Quernant			60	100		$V_{IN} = +3V$
Input Current	lin		120	200	μA	$V_{IN} = +5V$
Input Current while Overtemperature Active	—	_	—	220	μA	V _{IN} = +5V
Statia Dusia Courses On State Desistance			400	600		V _{IN} = +3V, I _D = 0.5A
Static Drain-Source On-State Resistance	RDS(ON)		350	500	mΩ	V _{IN} = +5V, I _D = 0.5A
Continuous Drain Current (Note 5)	ID	0.9	—	—		V _{IN} = 3V, T _A = +25°C
Continuous Drain Current (Note 5)		1.0	—	—	A	$V_{IN} = 5V, T_A = +25^{\circ}C$
Continuous Drain Current (Note 6)		1.2	—	—		V _{IN} = 3V, T _A = +25°C
Continuous Drain Current (Note 6)		1.3	—			$V_{IN} = 5V, T_A = +25^{\circ}C$
Current Limit (Note 9)	Id(LIM)	0.7	1.7	_	A	$V_{IN} = +3V$
Current Limit (Note 8)		1	2.2	—		$V_{IN} = +5V$
Dynamic Characteristics			•	•		
Turn-On Delay Time	td(on)		5			
Rise Time	t _R		10	_		
Turn-Off Delay Time	tD(OFF)	_	45	—	μs	V _{DD} = 12V, I _D = 0.5A, V _{GS} = 5V
Fall Time	f⊢	_	15	—		
Overtemperature Protection	·			•		
Thermal Overload Trip Temperature (Note 9)	TJT	+150	+175	_	°C	—
Thermal Hysteresis (Note 9)	fF		+10	—	°C	—

5. For a device surface mounted on 15mm x 15mm single sided, 1oz weight copper on 1.6mm FR4 board, in still air conditions. 6. For a device surface mounted on 50mm x 50mm single sided, 2oz weight copper on 1.6mm FR4 board, in still air conditions. Notes:

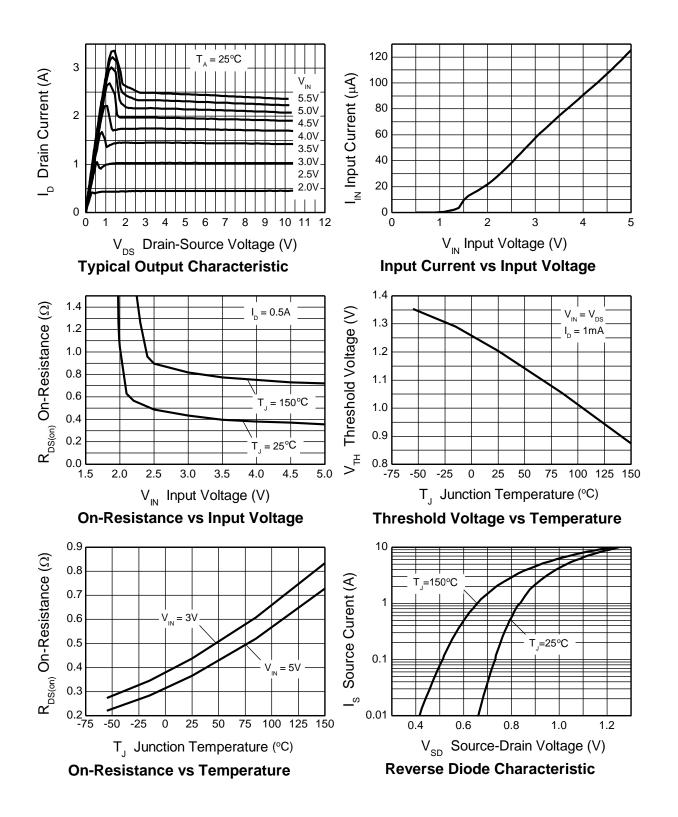
7. Thermal resistance from junction and the mounting surfaces of the drain pins.

8. The drain current is restricted only when the device is in saturation (see graph 'Typical Output Characteristic'). This allows the device to be used in the fully on-state without interference from the current limit. The device is fully protected at all drain currents, as the low power dissipation generated outside saturation makes current limit unnecessary.

9. Overtemperature protection is designed to prevent device destruction under fault conditions. Fault conditions are considered as "outside" normal operating range, so this part is not designed to withstand over-temperature for extended periods.

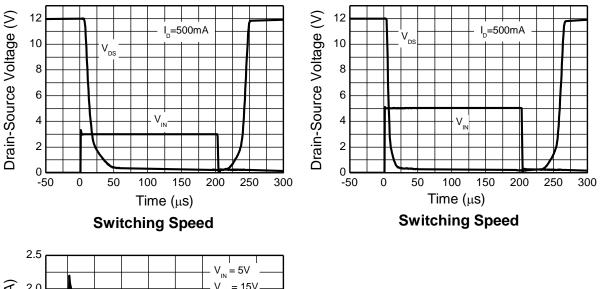


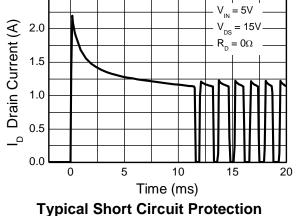
Typical Performance Characteristics





Typical Performance Characteristics (Continued)

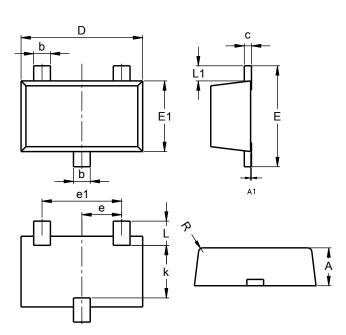






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

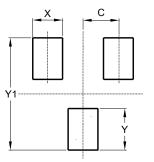


1	60)T23F			
Dim					
Dim	Min	Max	Тур		
Α	0.80	1.00	0.90		
A1	0.00	0.10	0.01		
b	0.35	0.50	0.44		
С	0.10	0.20	0.16		
D	2.80	3.00	2.90		
е	0.95 REF				
e1		1.90 RE	F		
Е	2.30	2.50	2.40		
E1	1.50	1.70	1.65		
k	1.20				
L	0.30	0.65	0.50		
L1	0.30	0.50	0.40		
R	0.05	0.15	-		
A	All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23F



Dimensions	Value (in mm)		
С	0.95		
Х	0.80		
Y	1.110		
Y1	3.000		



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